



BIPOLAR ANALOG INTEGRATED CIRCUIT $\mu PC8182TB$

3 V, 2.9 GHz SILICON MMIC MEDIUM OUTPUT POWER AMPLIFIER FOR MOBILE COMMUNICATIONS

DESCRIPTION

The μ PC8182TB is a silicon monolithic integrated circuit designed as amplifier for mobile communications. This IC operates at 3V. The medium output power is suitable for RF-TX of mobile communications system.

This IC is manufactured using NEC's 30 GHz f_{max} UHS0 (<u>U</u>Itra <u>High Speed Process</u>) silicon bipolar process. This process uses direct silicon nitride passivation film and gold electrodes. These materials can protect the chip surface from pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

FEATURES

High-density surface mounting	: 6-pin super minimold package ($2.0 \times 1.25 \times 0.9$ mm)
Supply voltage	: Vcc = 2.7 to 3.3 V
Circuit current	: Icc = 30 mA TYP. @ Vcc = 3.0 V
 Medium output power 	: Po(1dB) = +9.5 dBm TYP. @ f = 0.9 GHz
	Po(1dB) = +9.0 dBm TYP. @ f = 1.9 GHz
	Po(1dB) = +8.0 dBm TYP. @ f = 2.4 GHz
Power gain	: GP = 21.5 dB TYP. @ f = 0.9 GHz
	G _P = 20.5 dB TYP. @ f = 1.9 GHz
	G _P = 20.5 dB TYP. @ f = 2.4 GHz
Upper limit operating frequency	: fu = 2.9 GHz TYP. @ 3 dB bandwidth

APPLICATION

• Buffer amplifiers on 1.9 to 2.4 GHz mobile communications system.

ORDERING INFORMATION

Part Number	Package	Marking	Supplying Form
μPC8182TB-E3	6-pin super minimold	C3F	Embossed tape 8 mm wide. 1, 2, 3 pins face the perforation side of the tape. Qty 3 kpcs/reel.

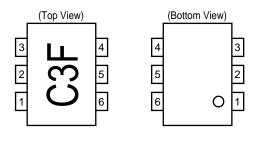
Remark To order evaluation samples, please contact your local NEC sales office.

(Part number for sample order: µPC8182TB)

Caution Electro-static sensitive devices

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PIN CONNECTIONS



Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	Vcc

PRODUCT LINE-UP (TA = +25°C, Vcc = Vout = 3.0 V, Zs = ZL = 50 Ω)

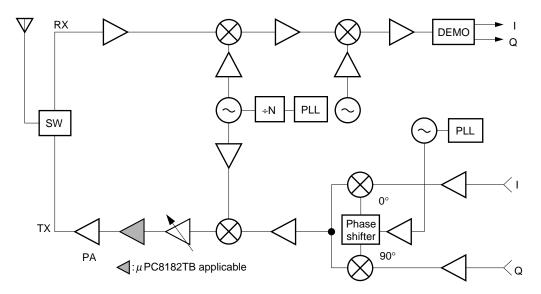
	Part No.	fu (GHz)	Po (1 dB) (dBm)	GP (dB)	Icc (mA)	Package	Marking
*	μPC8182TB	2.9	+9.5 @ f = 0.9 GHz	21.5 @ f = 0.9 GHz	30.0	6-pin super minimold	C3F
			+9.0 @ f = 1.9 GHz	20.5 @ f = 1.9 GHz			
			+8.0 @ f = 2.4 GHz	20.5 @ f = 2.4 GHz			
	μPC2762T	2.9	+8.0 @ f = 0.9 GHz	13.0 @ f = 0.9 GHz	26.5	6-pin minimold	C1Z
	μPC2762TB		+7.0 @ f = 1.9 GHz	15.5 @ f = 1.9 GHz		6-pin super minimold	
	μPC2763T	2.7	+9.5 @ f = 0.9 GHz	20.0 @ f = 0.9 GHz	27.0	6-pin minimold	C2A
	μPC2763TB		+6.5 @ f = 1.9 GHz	21.0 @ f = 1.9 GHz		6-pin super minimold	
	μPC2771T	2.2	+11.5 @ f = 0.9 GHz	21.0 @ f = 0.9 GHz	36.0	6-pin minimold	C2H
	μPC2771TB		+9.5 @ f = 1.5 GHz	21.0 @ f = 1.5 GHz		6-pin super minimold	

Remark Typical performance. Please refer to ELECTRICAL CHARACTERISTICS in detail.

Caution The package size distinguishes between minimold and super minimold.

SYSTEM APPLICATION EXAMPLE

Digital cellular telephone



Caution The insertion point is different due to the specifications of conjunct devices.

PIN EXPLANATION

	Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) ^{Note}	Function and Applications	Internal Equivalent Circuit
*	1	INPUT		0.99	Signal input pin. A internal matching circuit, configured with resistors, enables 50Ω connection over a wide band. A multi-feedback circuit is designed to cancel the deviations of hFE and resistance. This pin must be coupled to signal source with capacitor for DC cut.	6
	4	OUTPUT	Voltage as same as Vcc through external inductor	_	Signal output pin. The inductor must be attached between Vcc and output pins to supply current to the internal output transistors.	
	6	Vcc	2.7 to 3.3	_	Power supply pin, which biases the internal input transistor. This pin should be externally equipped with bypass capacitor to minimize its impedance.	
	2 3 5	GND	0	_	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance difference.	(3) (2)(5) GND GND

Note Pin voltage is measured at Vcc = 3.0 V.

***** ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc	$T_{A} = +25^{\circ}C$, pin 4 and 6	3.6	V
Total Circuit Current	lcc	TA = +25°C	60	mA
Power Dissipation	PD	Mounted on double copper clad $50 \times 50 \times 1.6$ mm epoxy glass PWB (TA = +85°C)	270	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		–55 to +150	°C
Input Power	Pin	$T_A = +25^{\circ}C$	+10	dBm

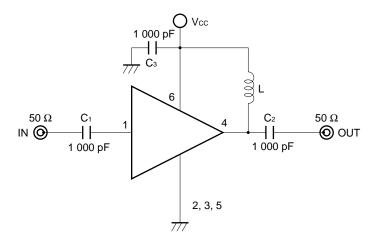
RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Remark
Supply Voltage	Vcc	2.7	3.0	3.3	V	Same voltage should be applied to pin 4 and 6.
Operating Ambient Temperature	Та	-40	+25	+85	°C	-

* ELECTRICAL CHARACTERISTICS (Unless otherwise specified, T_A = +25°C, V_{CC} = V_{out} = 3.0 V, Zs = ZL = 50 Ω)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	No signal	-	30.0	38.0	mA
Power Gain	GP	f = 0.9 GHz	19.0	21.5	25.0	dB
		f = 1.9 GHz	18.0	20.5	24.0	
		f = 2.4 GHz	18.0	20.5	24.0	
Noise Figure	NF	f = 0.9 GHz	-	4.5	6.0	dB
		f = 1.9 GHz	-	4.5	6.0	
		f = 2.4 GHz	-	5.0	6.5	
Upper Limit Operating Frequency	fu	3 dB down below from gain at f = 0.1 GHz	2.6	2.9	-	GHz
Isolation	ISL	f = 0.9 GHz	28	33	-	dB
		f = 1.9 GHz	27	32	-	
		f = 2.4 GHz	26	31	-	
Input Return Loss	RLin	f = 0.9 GHz	5	8	-	dB
		f = 1.9 GHz	7	10	-	
		f = 2.4 GHz	9	12	-	
Output Return Loss	RLout	f = 0.9 GHz	7	10	-	dB
		f = 1.9 GHz	8	11	-	
		f = 2.4 GHz	11	14	-	
Gain 1 dB Compression Output	PO (1dB)	f = 0.9 GHz	+7.0	+9.5	-	dBm
Power		f = 1.9 GHz	+6.5	+9.0	-	
		f = 2.4 GHz	+5.5	+8.0	-	
Saturated Output Power	PO (sat)	$f = 0.9 \text{ GHz}, P_{in} = -5 \text{ dBm}$	-	+11.0	-	dBm
		$f = 1.9 \text{ GHz}, P_{in} = -5 \text{ dBm}$	-	+10.5	-	
		$f = 2.4 \text{ GHz}, P_{in} = -5 \text{ dBm}$	_	+10.0	_	

TEST CIRCUIT



COMPONENTS OF TEST CIRCUIT FOR MEASURING ELECTRICAL CHARACTERISTICS

	Туре	Value
C1, C2	Bias Tee	1 000 pF
C₃	Capacitor	1 000 pF
L	Bias Tee	1 000 nH

 Type
 Value
 Operating Frequency

 C1 to C3
 Chip capacitor
 1 000 pF
 100 MHz or higher

 L
 Chip inductor
 100 nH
 100 MHz or higher

 10 nH
 2.0 GHz or higher

EXAMPLE OF ACTUAL APPLICATION COMPONENTS

INDUCTOR FOR THE OUTPUT PIN

The internal output transistor of this IC consumes 20 mA, to output medium power. To supply current for output transistor, connect an inductor between the Vcc pin (pin 6) and output pin (pin 4). Select large value inductance, as listed above.

The inductor has both DC and AC effects. In terms of DC, the inductor biases the output transistor with minimum voltage drop to output enable high level. In terms of AC, the inductor make output-port-impedance higher to get enough gain. In this case, large inductance and Q is suitable.

For above reason, select an inductance of 100 Ω or over impedance in the operating frequency. The gain is a peak in the operating frequency band, and suppressed at lower frequencies.

The recommendable inductance can be chosen from example of actual application components list as shown above.

CAPACITORS FOR THE Vcc, INPUT, AND OUTPUT PINS

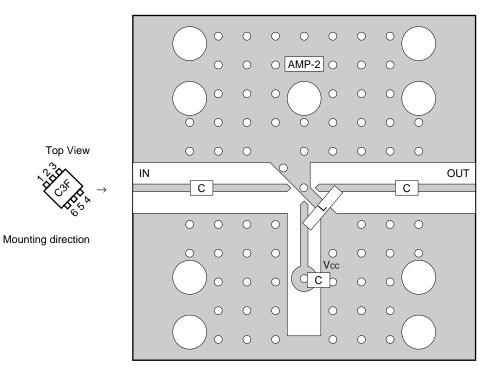
Capacitors of 1 000 pF are recommendable as the bypass capacitor for the Vcc pin and the coupling capacitors for the input and output pins.

The bypass capacitor connected to the Vcc pin is used to minimize ground impedance of Vcc pin. So, stable bias can be supplied against Vcc fluctuation.

The coupling capacitors, connected to the input and output pins, are used to cut the DC and minimize RF serial impedance. Their capacitance are therefore selected as lower impedance against a 50 Ω load. The capacitors thus perform as high pass filters, suppressing low frequencies to DC.

To obtain a flat gain from 100 MHz upwards, 1 000 pF capacitors are used in the test circuit. In the case of under 10 MHz operation, increase the value of coupling capacitor such as 10 000 pF. Because the coupling capacitors are determined by equation, $C = 1/(2\pi R fc)$.

ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD



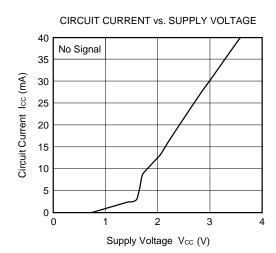
COMPONENT LIST

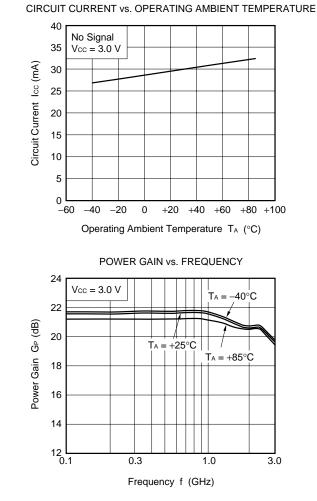
	Value
С	1 000 pF
L	Example: 10 nH

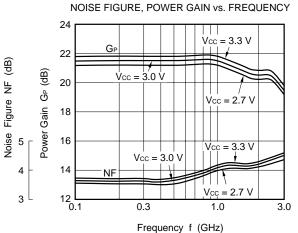
Notes

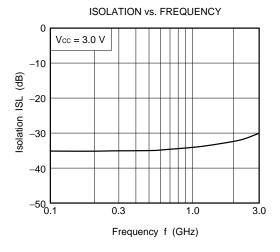
- 1. $30 \times 30 \times 0.4$ mm double sided copper clad polyimide board.
- 2. Back side: GND pattern
- 3. Solder plated on pattern
- 4. O O: Through holes

★ TYPICAL CHARACTERISTICS (Unless otherwise specified, T_A = +25°C)

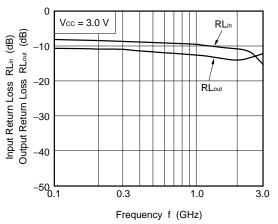


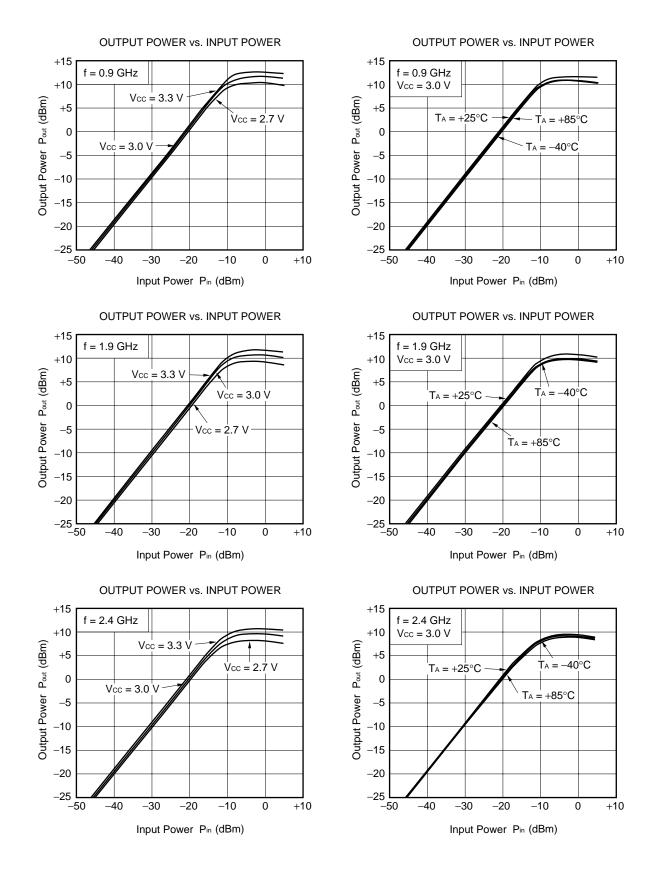


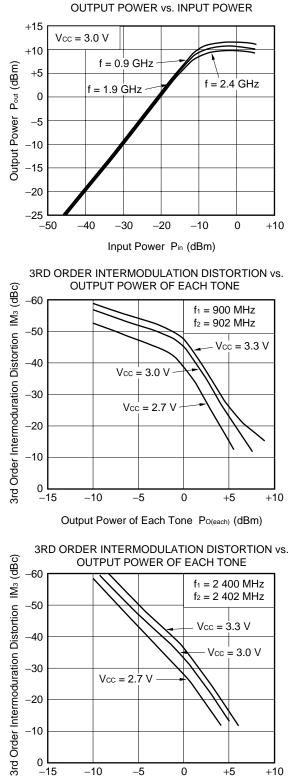


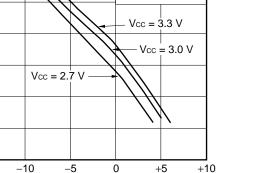


INPUT RETURN LOSS, OUTPUT RETURN LOSS vs. FREQUENCY











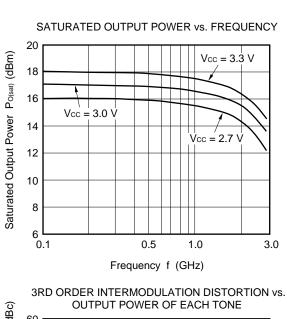
-20

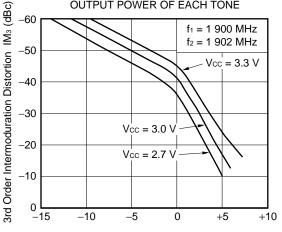
-10

0

_15

Remark The graphs indicate nominal characteristics.

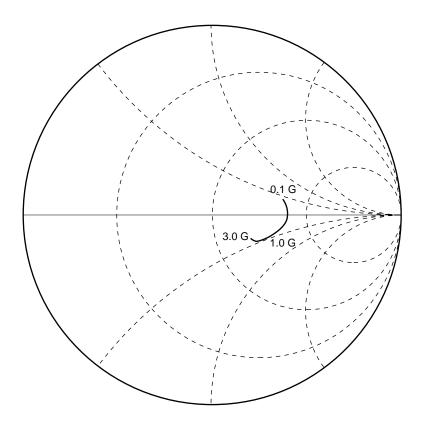




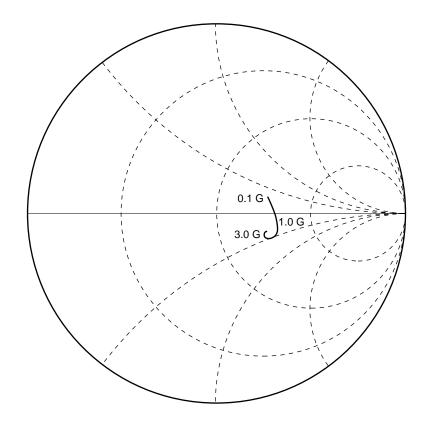
Output Power of Each Tone Po(each) (dBm)

* S-PARAMETERS (Vcc = Vout = 3.0 V)

S11-FREQUENCY



S22-FREQUENCY



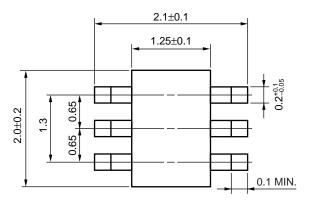
★ TYPICAL S-PARAMETER VALUES (T_A = +25°C)

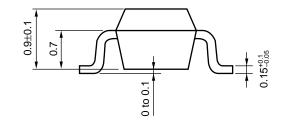
 $Vcc = V_{out} = 3.0 V$, Icc = 30 mA

FREQUENCY	S1	1	S	S 21	S	12	S	22	к
MHz	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	
100.0000	0.391	-2.6	12.933	-4.4	0.016	1.8	0.293	-2.7	1.84
200.0000	0.391	-6.2	12.999	-8.0	0.017	3.5	0.287	-5.1	1.80
300.0000	0.387	-10.2	13.174	-11.8	0.016	7.6	0.282	-6.8	1.86
400.0000	0.382	-13.8	13.322	-16.4	0.016	9.2	0.279	-8.4	1.82
500.0000	0.371	-16.7	13.391	-20.7	0.017	13.2	0.276	-9.1	1.79
600.0000	0.365	-19.5	13.407	-25.7	0.017	15.9	0.279	-10.0	1.78
700.0000	0.354	-21.6	13.549	-30.4	0.018	21.0	0.278	-11.0	1.73
800.0000	0.347	-23.7	13.475	-35.3	0.020	22.3	0.285	-11.7	1.57
900.0000	0.343	-25.8	13.426	-40.1	0.020	21.2	0.290	-13.5	1.52
1000.0000	0.334	-28.1	13.474	-44.9	0.019	27.0	0.293	-15.1	1.62
1100.0000	0.330	-30.8	13.386	-50.0	0.018	28.1	0.296	-17.6	1.69
1200.0000	0.324	-32.1	13.185	-54.6	0.020	27.6	0.302	-20.3	1.61
1300.0000	0.317	-34.2	13.121	-59.4	0.020	31.7	0.303	-21.9	1.62
1400.0000	0.318	-35.7	13.151	-64.2	0.021	32.1	0.309	-24.6	1.51
1500.0000	0.313	-38.0	12.866	-69.4	0.022	34.0	0.315	-27.1	1.47
1600.0000	0.309	-39.8	12.814	-73.9	0.023	34.6	0.318	-29.5	1.43
1700.0000	0.303	-42.5	12.508	-78.2	0.022	34.3	0.314	-33.1	1.52
1800.0000	0.302	-44.3	12.357	-83.2	0.024	35.9	0.319	-35.6	1.44
1900.0000	0.298	-45.5	12.090	-86.7	0.026	36.9	0.322	-37.6	1.39
2000.0000	0.290	-47.5	12.035	-90.9	0.025	40.0	0.313	-40.5	1.43
2100.0000	0.291	-50.1	11.984	-95.4	0.027	36.5	0.321	-43.5	1.36
2200.0000	0.283	-52.6	11.662	-99.9	0.026	38.2	0.314	-46.0	1.43
2300.0000	0.277	-54.1	11.711	-104.0	0.027	40.0	0.310	-48.6	1.41
2400.0000	0.274	-56.7	11.629	-108.6	0.028	38.4	0.309	-51.6	1.37
2500.0000	0.270	-58.0	11.475	-113.7	0.029	39.1	0.304	-54.1	1.35
2600.0000	0.261	-59.8	11.308	-118.5	0.029	39.9	0.297	-55.3	1.39
2700.0000	0.264	-61.4	11.198	-123.5	0.032	38.6	0.303	-56.5	1.29
2800.0000	0.253	-62.0	10.803	-129.4	0.031	42.8	0.295	-57.3	1.39
2900.0000	0.258	-63.9	10.670	-134.8	0.032	41.3	0.307	-57.9	1.33
3000.0000	0.255	-65.7	10.086	-139.5	0.033	40.9	0.316	-60.0	1.35
3100.0000	0.250	-67.9	9.683	-145.4	0.032	39.8	0.321	-63.1	1.44

***** PACKAGE DIMENSIONS

6-PIN SUPER MINIMOLD (UNIT: mm)





NOTES ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to the Vcc pin.
- (4) The inductor must be attached between Vcc and output pins. The inductance value should be determined in accordance with desired frequency.
- (5) The DC cut capacitor must be attached to input and output pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235°C or below Time: 30 seconds or less (at 210°C) Count: 3, Exposure limit: None ^{Note}	IR35-00-3
VPS	Package peak temperature: 215°C or below Time: 40 seconds or less (at 200°C) Count: 3, Exposure limit: None ^{Note}	VP15-00-3
Wave Soldering	Soldering bath temperature: 260°C or below Time: 10 seconds or less Count: 1, Exposure limit: None ^{Note}	WS60-00-1
Partial Heating	Pin temperature: 300°C Time: 3 seconds or less (per side of device) Exposure limit: None ^{Note}	_

Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document **SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E)**.



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